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	Data Sheet
	2N458A
Semiconductor Corp. 145 Adams Avenue, Hauppauge, NY 11788 USA	PNP GERMANIUM POWER TRANSISTOR
Tel: (631) 435-1110 • Fax: (631) 435-1824	JEDEC TO-3 CASE
Manufacturers of World Class Discrete Semiconductors	

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N458A type is a PNP Germanium Alloy Junction Power Transistor manufacture in a hermetically sealed metal case, designed for high voltage amplifier and switching circuits.

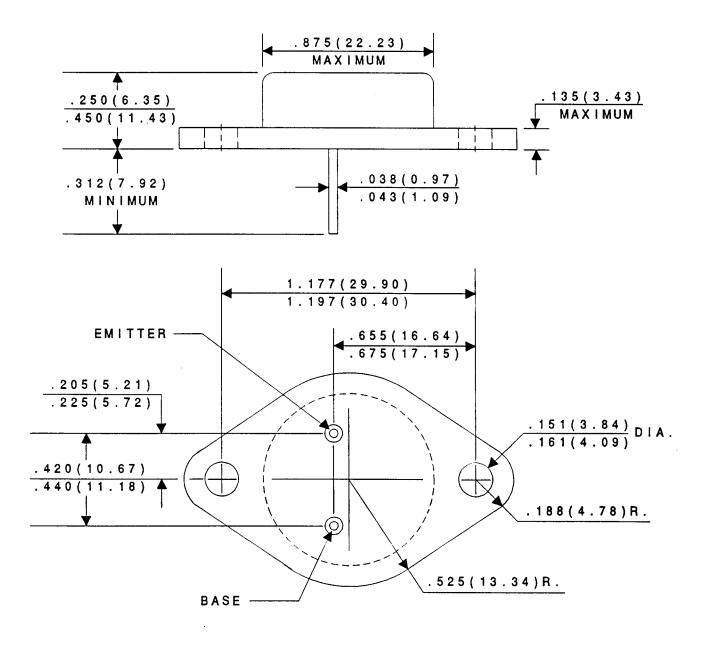
<u>MAXIMUM RATINGS</u> $(T_C = 25 °C)$

_	SYMBOL		<u>UNITS</u>
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	30	V
Collector Current	IC	7.0	А
Base Current	۱ _B	3.0	А
Power Dissipation	PD	150	W
Operating and Storage			
Junction Temperature	T _J ,T _{stg}	-55 to +100	°C
Thermal Resistance	Θ ^{LG}	0.5	°C/W

<u>ELECTRICAL CHARACTERISTICS</u> ($T_C = 25 \,^{\circ}C$ unless otherwise noted)

<u>SYMBOL</u>	TEST CONDITIONS	MIN	MAX	<u>UNITS</u>
Ісво	V _{CB} =40V		0.5	mA
ICBO	V _{CB} = 80V		2.0	mA
BVCBO	I _C = 2.0mA	80		V
BVCES	I _C = 50mA	65		V
BV _{EBO}	I _E = 2.0mA	30		V
BVCER	$I_{C} = 50 \text{mA}, R_{BE} = 33\Omega$	67		V
BVCEO	I _C = 50mA	45		V
V _{CE} (SAT)	I _C = 5.0A, I _B = 500mA		0.5	V
V _{BE(ON)}	$V_{CE} = 1.5V, I_{C} = 5.0A$		1.5	V
h _{FE}	$V_{CE} = 1.5V, I_{C} = 1.0A$	40		
hFE	$V_{CE} = 1.5V, I_{C} = 3.0A$	35		
h _{FE}	$V_{CE} = 1.5V, I_{C} = 5.0A$	30	90	
h _{FE}	$V_{CE} = 1.5V, I_{C} = 7.0A$	22		
fŢ	$V_{CE} = 2.0V, I_{C} = 1.0A$	200		kHz

JEDEC TO-3 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).